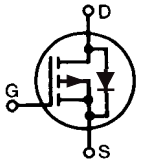
# IXYS

## TrenchP™ Power MOSFETs

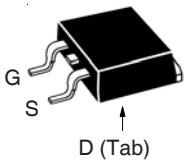
## IXTA24P085T
## IXTP24P085T

$V_{DSS}$ = - 85V
$I_{D25}$ = - 24A
$R_{DS(on)}$ ≤ 65mΩ

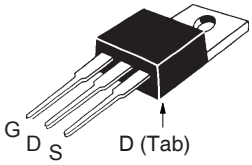
P-Channel Enhancement Mode
Avalanche Rated




**TO-263 AA (IXTA)**




**TO-220AB (IXTP)**




G = Gate D = Drain
S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|---|---|---|---|
| $V_{DSS}$ | $T_J$ = 25°C to 150°C | - 85 | V |
| $V_{DGR}$ | $T_J$ = 25°C to 150°C, $R_{GS}$ = 1MΩ | - 85 | V |
| $V_{GSS}$ | Continuous | ±15 | V |
| $V_{GSM}$ | Transient | ±25 | V |
| $I_{D25}$ | $T_C$ = 25°C | - 24 | A |
| $I_{DM}$ | $T_C$ = 25°C, Pulse Width Limited by $T_{JM}$ | - 80 | A |
| $I_A$ | $T_C$ = 25°C | - 24 | A |
| $E_{AS}$ | $T_C$ = 25°C | 200 | mJ |
| $P_D$ | $T_C$ = 25°C | 83 | W |
| $T_J$ | | -55 ... +150 | °C |
| $T_{JM}$ | | 150 | °C |
| $T_{stg}$ | | -55 ... +150 | °C |
| $T_L$ | 1.6mm (0.062 in.) from Case for 10s | 300 | °C |
| $T_{SOLD}$ | Plastic Body for 10s | 260 | °C |
| $M_d$ | Mounting Torque (TO-220) | 1.13/10 | Nm/lb.in. |
| **Weight** | TO-220 | 3.0 | g |
| | TO-263 | 2.5 | g |

### Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and $Q_G$

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

| Symbol | Test Conditions ($T_J$ = 25°C, Unless Otherwise Specified) | Characteristic Values Min. | Typ. | Max. | |
|---|---|---|---|---|---|
| $BV_{DSS}$ | $V_{GS}$ = 0V, $I_D$ = - 250μA | - 85 | | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D$ = - 250μA | - 2.5 | | - 4.5 | V |
| $I_{GSS}$ | $V_{GS}$ = ±15V, $V_{DS}$ = 0V | | | ±50 | nA |
| $I_{DSS}$ | $V_{DS} = V_{DSS}$, $V_{GS}$ = 0V | | | - 3 | μA |
| | $T_J$ = 125°C | | | -100 | μA |
| $R_{DS(on)}$ | $V_{GS}$ = -10V, $I_D = 0.5 \bullet I_{D25}$, Note 1 | | | 65 | mΩ |

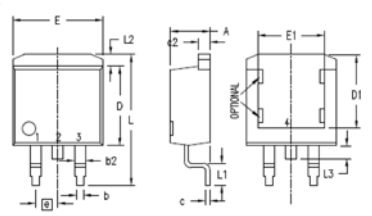
| Symbol | Test Conditions ($T_J$ = 25°C, Unless Otherwise Specified) | Characteristic Values Min. | Typ. | Max. | |
|---|---|---|---|---|---|
| $g_{fs}$ | $V_{DS}$ = -10V, $I_D$ = 0.5 • $I_{D25}$, Note 1 | 10 | 16 | | S |
| $C_{iss}$ | $V_{GS}$ = 0V, $V_{DS}$ = - 25V, f = 1MHz | | 2090 | | pF |
| $C_{oss}$ | | | 243 | | pF |
| $C_{rss}$ | | | 117 | | pF |
| $t_{d(on)}$ | **Resistive Switching Times** | | 18 | | ns |
| $t_r$ | $V_{GS}$ = -10V, $V_{DS}$ = 0.5 • $V_{DSS}$, $I_D$ = 0.5 • $I_{D25}$ | | 26 | | ns |
| $t_{d(off)}$ | $R_G$ = 10Ω (External) | | 53 | | ns |
| $t_f$ | | | 26 | | ns |
| $Q_{g(on)}$ | $V_{GS}$ = -10V, $V_{DS}$ = 0.5 • $V_{DSS}$, $I_D$ = 0.5 • $I_{D25}$ | | 41 | | nC |
| $Q_{gs}$ | | | 17 | | nC |
| $Q_{gd}$ | | | 11 | | nC |
| $R_{thJC}$ | | | | 1.5 | °C/W |
| $R_{thCS}$ | TO-220 | | 0.50 | | °C/W |

**Source-Drain Diode**

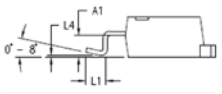
| Symbol | Test Conditions ($T_J$ = 25°C, Unless Otherwise Specified) | Characteristic Values Min. | Typ. | Max. | |
|---|---|---|---|---|---|
| $I_S$ | $V_{GS}$ = 0V | | | - 24 | A |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$ | | | - 96 | A |
| $V_{SD}$ | $I_F$ = - 24A, $V_{GS}$ = 0V, Note 1 | | | -1.5 | V |
| $t_{rr}$ | $I_F$ = -12A, -di/dt = -100A/μs | | 40 | | ns |
| $Q_{RM}$ | $V_R$ = - 43V, $V_{GS}$ = 0V | | 72 | | nC |
| $I_{RM}$ | | | - 3.6 | | A |

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

**TO-263 Outline**

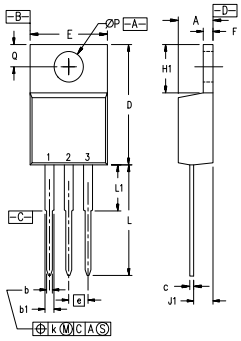


Pins:
1 - Gate
2,4 - Drain
3 - Source



| SYM | INCHES MIN | INCHES MAX | MILLIMETERS MIN | MILLIMETERS MAX |
|---|---|---|---|---|
| A | .160 | .190 | 4.06 | 4.83 |
| A1 | .080 | .110 | 2.03 | 2.79 |
| b | .020 | .039 | 0.51 | 0.99 |
| b2 | .045 | .055 | 1.14 | 1.40 |
| c | .016 | .029 | 0.40 | 0.74 |
| c2 | .045 | .055 | 1.14 | 1.40 |
| D | .340 | .380 | 8.64 | 9.65 |
| D1 | .315 | .350 | 8.00 | 8.89 |
| E | .380 | .410 | 9.65 | 10.41 |
| E1 | .245 | .320 | 6.22 | 8.13 |
| e | .100 BSC | | 2.54 BSC | |
| L | .575 | .625 | 14.61 | 15.88 |
| L1 | .090 | .110 | 2.29 | 2.79 |
| L2 | .040 | .055 | 1.02 | 1.40 |
| L3 | .050 | .070 | 1.27 | 1.78 |
| L4 | 0 | .005 | 0 | 0.13 |

**TO-220 Outline**



Pins: 1 - Gate 2 - Drain
3 - Source

| SYM | INCHES MIN | INCHES MAX | MILLIMETERS MIN | MILLIMETERS MAX |
|---|---|---|---|---|
| A | .170 | .190 | 4.32 | 4.83 |
| b | .025 | .040 | 0.64 | 1.02 |
| b1 | .045 | .065 | 1.15 | 1.65 |
| c | .014 | .022 | 0.35 | 0.56 |
| D | .580 | .630 | 14.73 | 16.00 |
| E | .390 | .420 | 9.91 | 10.66 |
| e | .100 BSC | | 2.54 BSC | |
| F | .045 | .055 | 1.14 | 1.40 |
| H1 | .230 | .270 | 5.85 | 6.85 |
| J1 | .090 | .110 | 2.29 | 2.79 |
| k | 0 | .015 | 0 | 0.38 |
| L | .500 | .550 | 12.70 | 13.97 |
| L1 | .110 | .230 | 2.79 | 5.84 |
| ØP | .139 | .161 | 3.53 | 4.08 |
| Q | .100 | .125 | 2.54 | 3.18 |

**Fig. 1. Output Characteristics @ $T_J$ = 25ºC**

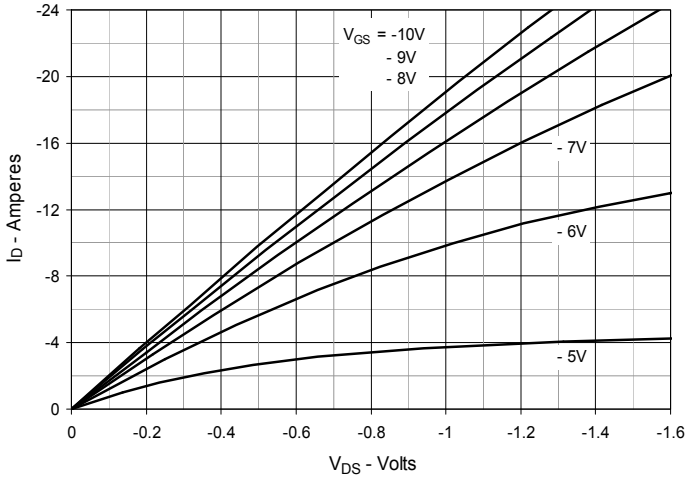



**Fig. 2. Extended Output Characteristics @ $T_J$ = 25ºC**

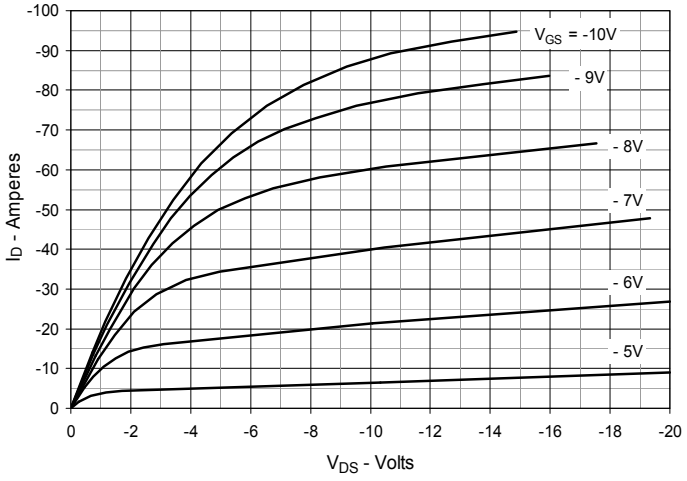



**Fig. 3. Output Characteristics @ $T_J$ = 125ºC**

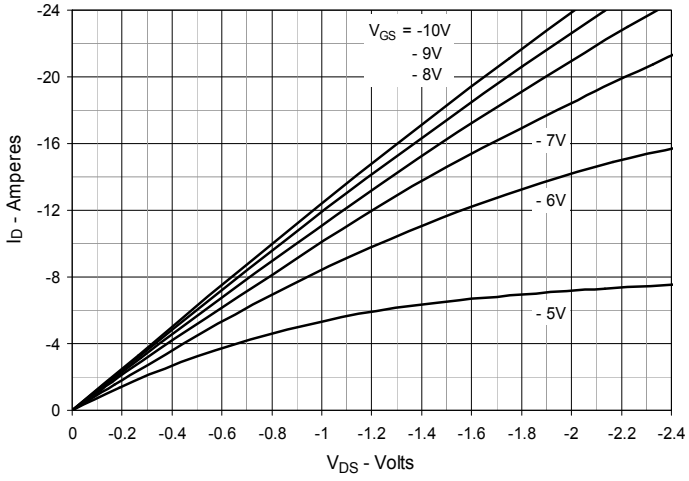



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D$ = -12A Value vs. Junction Temperature**

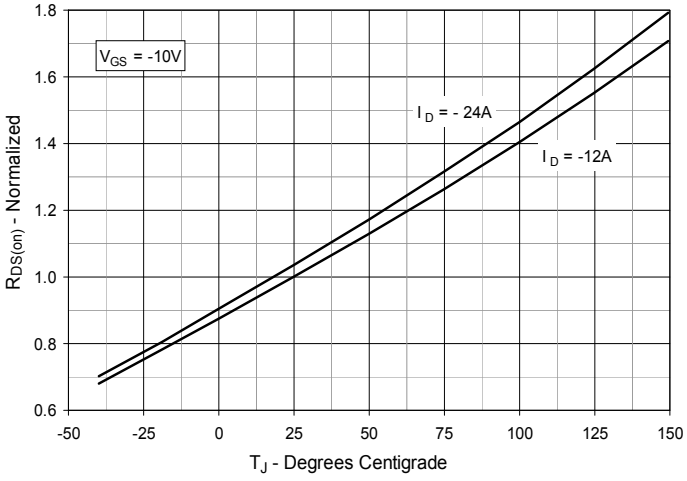



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D$ = -12A Value vs. Drain Current**

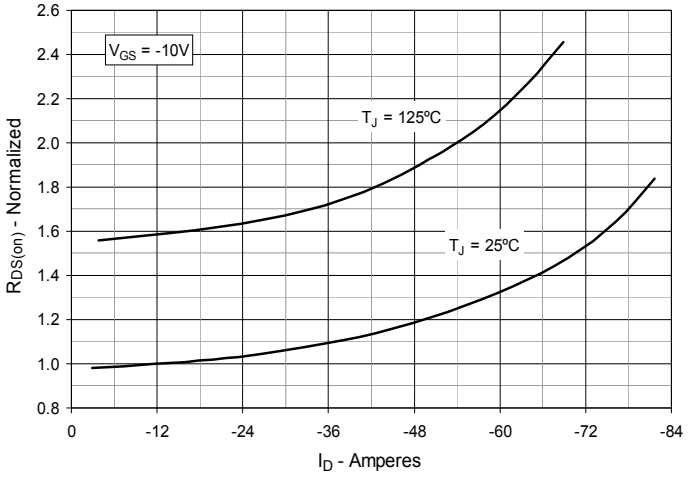



**Fig. 6. Maximum Drain Current vs. Case Temperature**

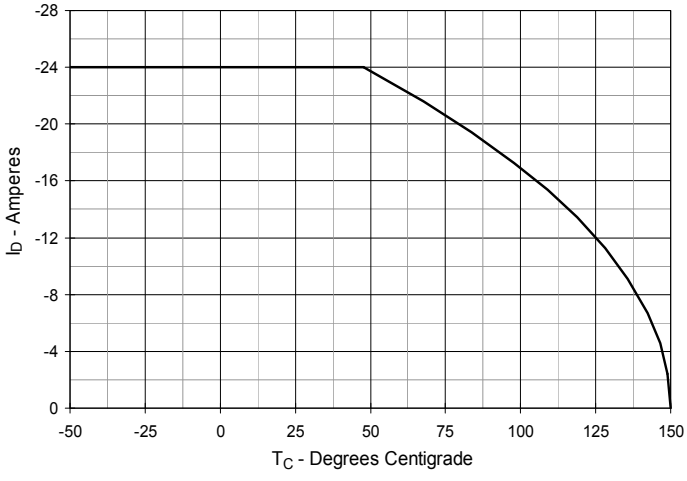


**Fig. 7. Input Admittance**

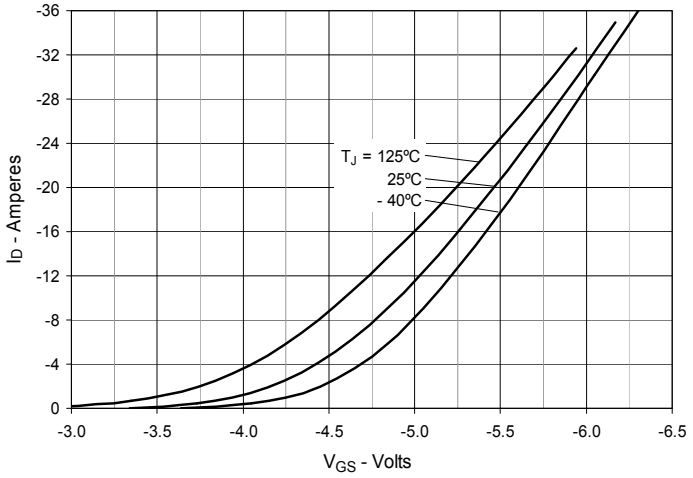



**Fig. 8. Transconductance**

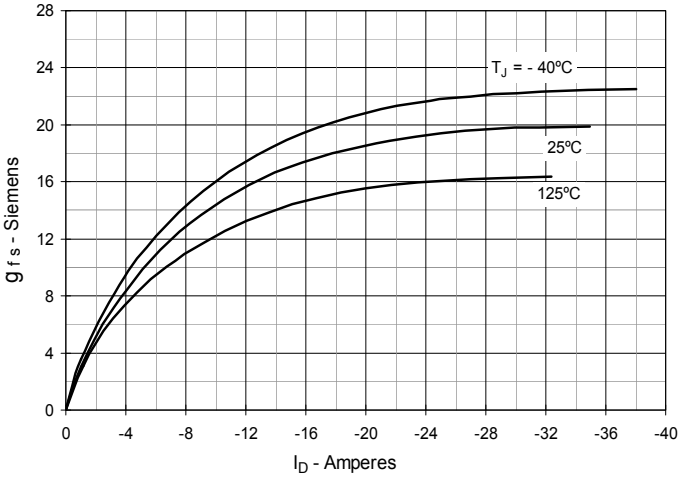



**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

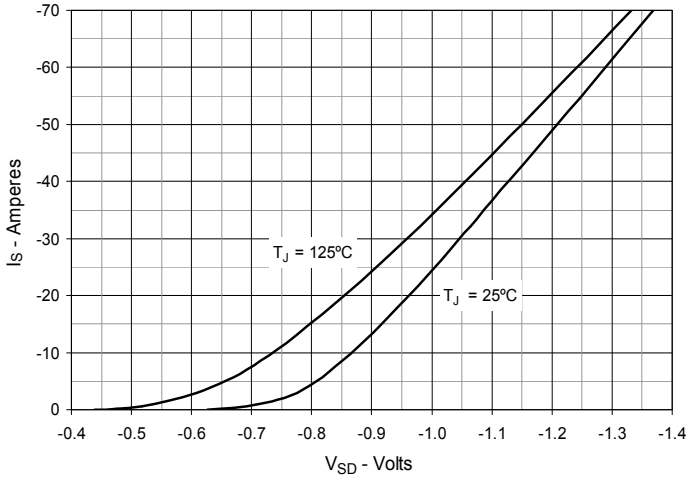



**Fig. 10. Gate Charge**

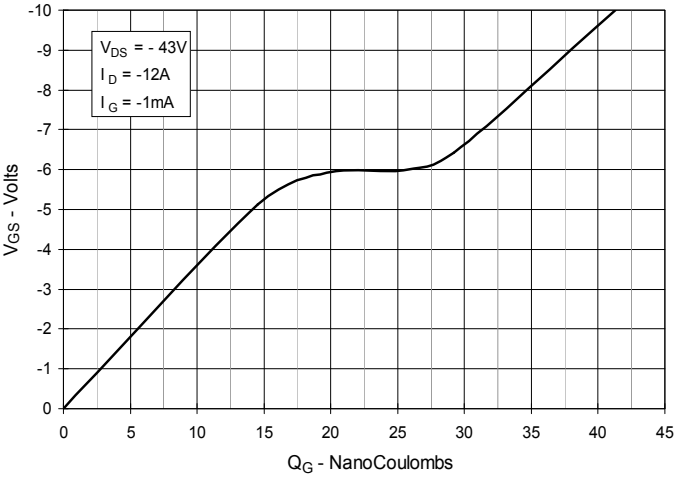



**Fig. 11. Capacitance**

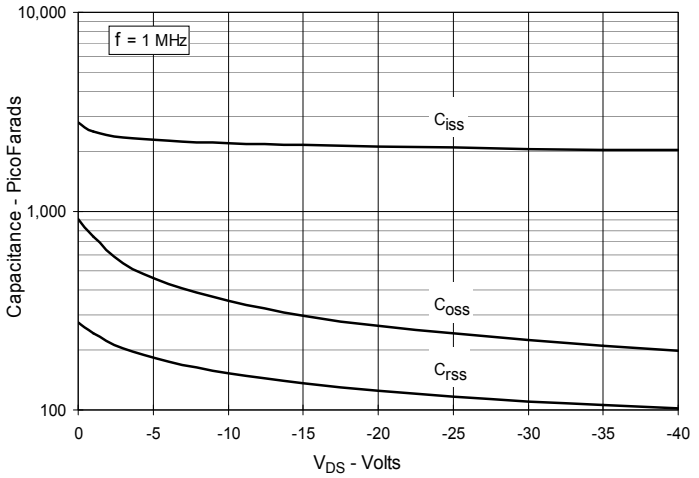



**Fig. 12. Forward-Bias Safe Operating Area**

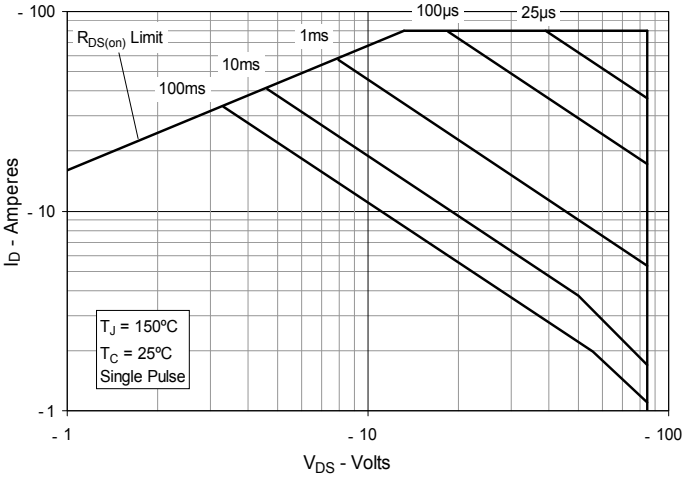


**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**

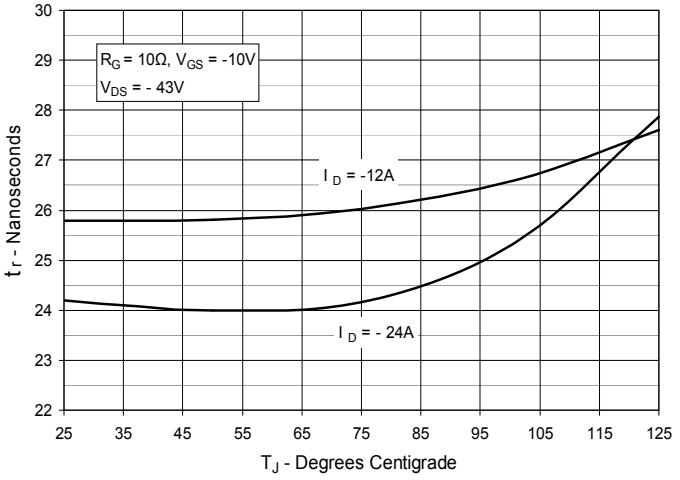



**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**

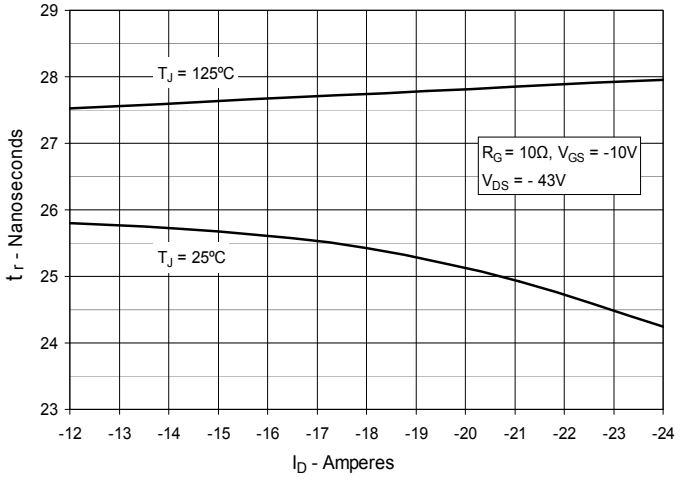



**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**

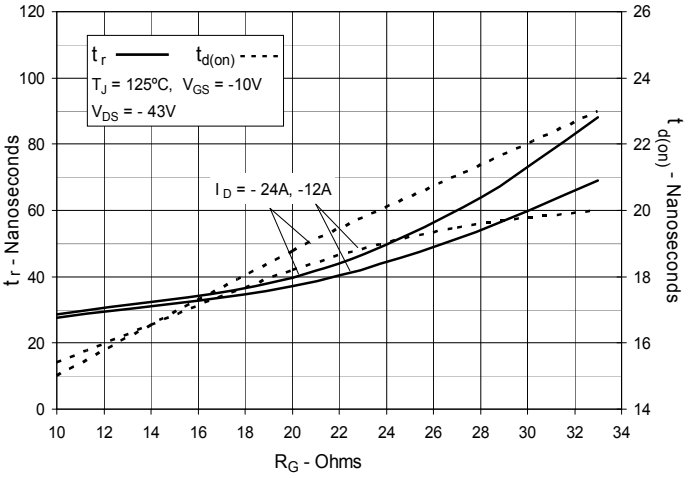



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**

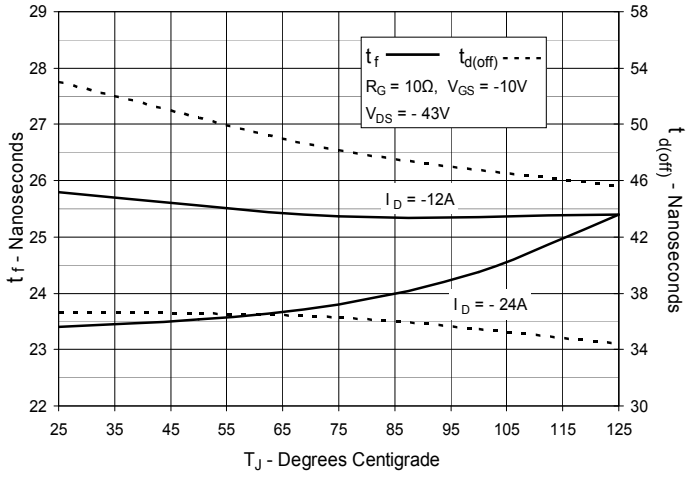



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**

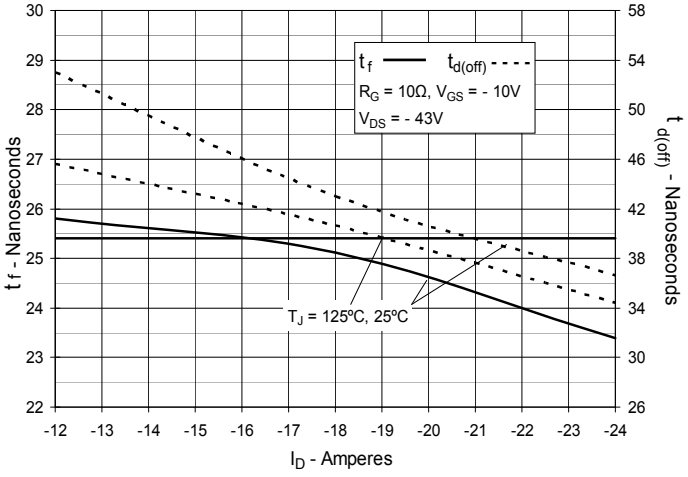



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

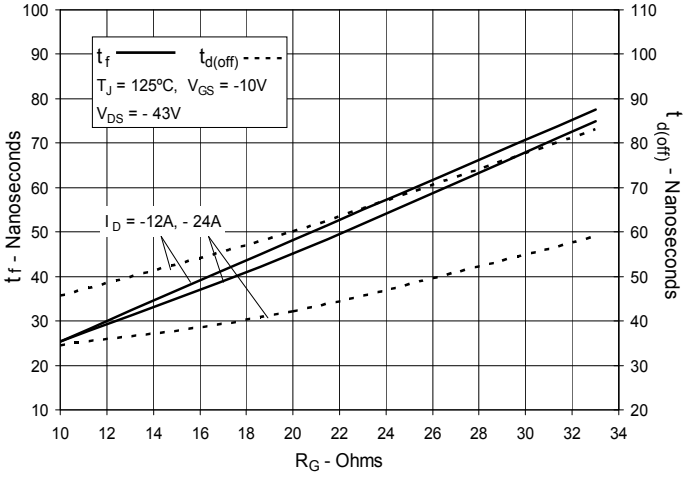


**Fig. 19. Maximum Transient Thermal Impedance**